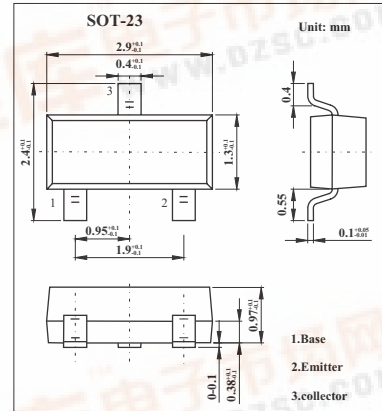


SMD Type Transistors

Medium Power Transistor  
FMMT555



Features

- 150 Volt  $V_{CE0}$
- 1 Amp continuous current

Absolute Maximum Ratings  $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-160	V
Collector-emitter voltage	$V_{CEO}$	-150	V
Emitter-base voltage	$V_{EBO}$	-5	V
Peak collector current	$I_{CM}$	-2	A
Collector current	$I_C$	-1	A
Base current	$I_B$	-200	mA
Power dissipation	$P_{tot}$	500	mW
Operating and storage temperature range	$T_j, T_{stg}$	-55 to +150	$^\circ C$

Electrical Characteristics  $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A$	-160			V
Collector-emitter breakdown voltage *	$V_{(BR)CEO}$	$I_C = -10mA$	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A$	-5			V
Collector cutoff current	$I_{CBO}$	$V_{CB} = -140V$			-0.1	$\mu A$
		$V_{CB} = -140V, T_a = 100^\circ C$			-10	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -4V$			-0.1	$\mu A$
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$			-0.3	V
Base-emitter saturation voltage *	$V_{BE(sat)}$	$I_C = -100mA, I_B = -10mA$			-1	V
Base-Emitter Turn-on Voltage *	$V_{BE(ON)}$	$I_C = -100mA, V_{CE} = -10V$			-1	V
Static Forward Current Transfer Ratio	$h_{FE}$	$I_C = -10mA, V_{CE} = -10V$	50		300	
		$I_C = -300mA, V_{CE} = -10V$	50			
Transition Frequency	$f_T$	$I_C = -50mA, V_{CE} = -10V, f = 100MHz$	100			MHz
Output capacitance	$C_{obo}$	$V_{CB} = -10V, f = 1MHz$			10	pF

\* Pulse test:  $t_p = 300 \mu s; d \leq 0.02.$

Marking

Marking	555
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